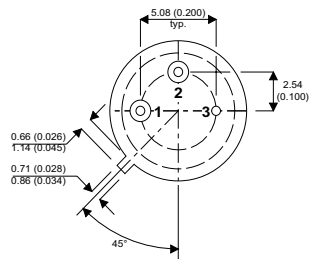
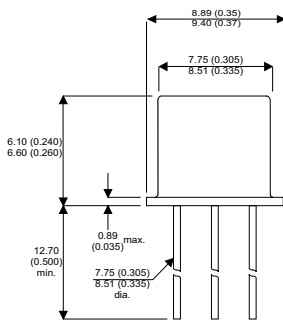


MECHANICAL DATA

Dimensions in mm (inches)


TO39 – Package

Pin 1 – Source Pin 2 – Gate Pin 3 – Drain

Also available in a low profile version.

**N-CHANNEL
POWER MOSFET**
 BV_{DSS} 500V
 $I_{D(cont)}$ 1.5
 $R_{DS(on)}$ 3.0Ω
FEATURES

- AVALANCHE ENERGY RATED
- HERMETICALLY SEALED
- DYNAMIC dv/dt RATING
- SIMPLE DRIVE REQUIREMENTS

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{GS}	Gate – Source Voltage	±20V
I_D	Continuous Drain Current ($V_{GS} = 10V$, $T_{case} = 25^{\circ}C$)	1.5A
I_D	Continuous Drain Current ($V_{GS} = 10V$, $T_{case} = 100^{\circ}C$)	1A
I_{DM}	Pulsed Drain Current ¹	6.5A
P_D	Power Dissipation @ $T_{case} = 25^{\circ}C$	20W
	Linear Derating Factor	0.16W/°C
E_{AS}	Single Pulse Avalanche Energy ²	0.11mJ
dv/dt	Peak Diode Recovery ³	3.5V/ns
T_J, T_{stg}	Operating and Storage Temperature Range	-55 to 150°C
$R_{\theta JC}$	Thermal Resistance Junction to Case	6.25°C/W
$R_{\theta JCA}$	Thermal Resistance Junction-to-Ambient	175°C/W

Notes

- 1) Pulse Test: Pulse Width $\leq 300\mu s$, $\delta \leq 2\%$
- 2) @ $V_{DD} = 50V$, $L \geq 0.100mH$, $R_G = 25\Omega$, Peak $I_L = 1.5A$, Starting $T_J = 25^{\circ}C$
- 3) @ $I_{SD} \leq 1.5A$, $di/dt \leq 50A/\mu s$, $V_{DD} \leq BV_{DSS}$, $T_J \leq 150^{\circ}C$, SUGGESTED $R_G = 7.5\Omega$

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
STATIC ELECTRICAL RATINGS					
BV_{DSS}	Drain – Source Breakdown Voltage	$V_{GS} = 0$	$I_D = 1\text{mA}$	500	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	Reference to 25°C $I_D = 1\text{mA}$		0.43	$\text{V}/^{\circ}\text{C}$
$R_{DS(on)}$	Static Drain – Source On–State Resistance	$V_{GS} = 10\text{V}$	$I_D = 1\text{A}$		3
		$V_{GS} = 10\text{V}$	$I_D = 1.5\text{A}$		3.45
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$	$I_D = 250\mu\text{A}$	2	4
g_{fs}	Forward Transconductance	$V_{DS} \geq 15\text{V}$	$I_{DS} = 1\text{A}$	1	$\text{S}(\bar{\omega})$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0$	$V_{DS} = 0.8BV_{DSS}$ $T_J = 125^{\circ}\text{C}$		25
					250
I_{GSS}	Forward Gate – Source Leakage	$V_{GS} = 20\text{V}$			100
I_{GSS}	Reverse Gate – Source Leakage	$V_{GS} = -20\text{V}$			-100
DYNAMIC CHARACTERISTICS					
C_{iss}	Input Capacitance	$V_{GS} = 0$			350
C_{oss}	Output Capacitance	$V_{DS} = 25\text{V}$			80
C_{riss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$			35
Q_g	Total Gate Charge	$V_{GS} = 10\text{V}$	$I_D = 1.5\text{A}$	7.3	16.7
Q_{gs}	Gate – Source Charge	$V_{DS} = 0.5BV_{DS}$			3
Q_{gd}	Gate – Drain (“Miller”) Charge	$I_D = 1.5\text{A}$		0.1	3
$t_{d(on)}$	Turn–On Delay Time	$V_{DS} = 0.5BV_{DS}$			8.7
t_r	Rise Time	$V_{DD} = 250\text{V}$			40
$t_{d(off)}$	Turn–Off Delay Time	$I_D = 1.5\text{A}$			30
t_f	Fall Time	$R_G = 7.5\Omega$			60
					30
SOURCE – DRAIN DIODE CHARACTERISTICS					
I_S	Continuous Source Current				1.5
I_{SM}	Pulse Source Current ²				6.5
V_{SD}	Diode Forward Voltage	$I_S = 1.5\text{A}$	$T_J = 25^{\circ}\text{C}$		1.2
		$V_{GS} = 0$			
t_{rr}	Reverse Recovery Time	$I_F = 1.5\text{A}$	$T_J = 25^{\circ}\text{C}$		900
Q_{rr}	Reverse Recovery Charge	$d_i / d_t \leq 100\text{A}/\mu\text{s}$			5.9
		$V_{DD} \leq 50\text{V}$			
t_{on}	Forward Turn–On Time			Negligible	
PACKAGE CHARACTERISTICS					
L_D	Internal Drain Inductance (from centre of drain pad to die)			5.0	nH
L_S	Internal Source Inductance (from centre of source pad to end of source bond wire)			15.0	

Notes

- 1) Pulse Test: Pulse Width $\leq 300\mu\text{s}$, $\delta \leq 2\%$
- 2) Repetitive Rating – Pulse width limited by maximum junction temperature.